

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) Composition for the production of semiconductors, comprising H_2SiF_6 and/or HBF_4 in a total amount of 10 – 500 mg/kg, 12 – 17% by weight of H_2SO_4 , 2 – 4% by weight of H_2O_2 , optionally in combination with additives, in aqueous solution.
2. (Original) Use of a composition comprising H_2SiF_6 and/or HBF_4 as residual polymer remover in a process step in the production of semiconductors.
3. (Original) Use according to Claim 2 for the removal of residual polymers from Al or Al-containing conductor tracks.
4. (Original) Use according to Claim 2 for the removal of residual polymers after dry etching on metal conductor tracks and contact holes.
5. (Original) Use of a composition according to Claim 1 for the removal of residual polymers from aluminium or copper/aluminium alloys.
6. (Currently Amended) Use of a composition comprising H_2SiF_6 and/or HBF_4 in a total amount of 10 – 500 mg/kg, 12 – 17% by weight of H_2SO_4 , 2 – 4% by weight of H_2O_2 , optionally in combination with additives, in aqueous solution, according to ~~one or more of Claims 2–5~~ Claim 2.
7. (Currently Amended) Use according to ~~one or more of Claims 2–6~~ Claim 2 for the removal of residual polymers in a process step in the production of semiconductors using a spin etcher or in a tank unit.
8. (Original) Process for the removal of residual polymers from Al or Al-containing conductor tracks, characterised in that residual polymers are removed using a composition according to Claim 1.